SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

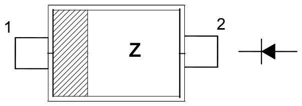
for rectifying small power applications

Features

- Ultra small mold type
- Low forward voltage
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



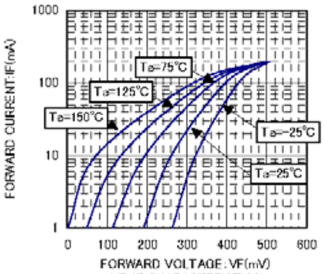
Top View
Marking Code: "Z"
Simplified outline SOD-323 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

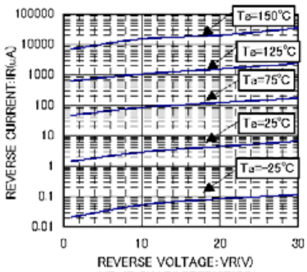
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

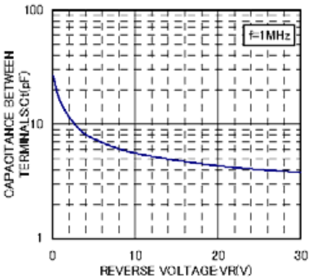
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 10 mA at I_F = 100 mA at I_F = 200 mA	V_F	0.16 0.31 0.41	0.3 0.45 0.54	V
Reverse Current at V_R = 10 V at V_R = 40 V	I_R	- -	20 90	μA



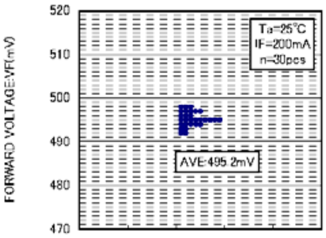
VF-IF CHARACTERISTICS



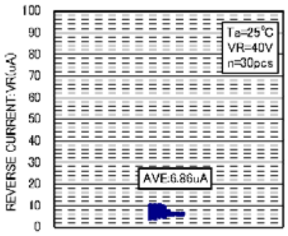
VR-IR CHARACTERISTICS



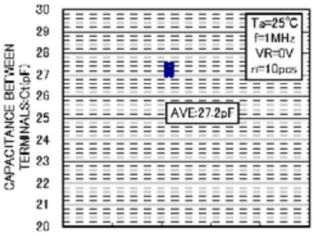
VR-Ct CHARACTERISTICS



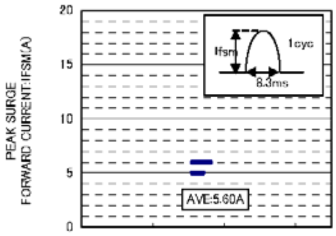
VF DISPERSION MAP



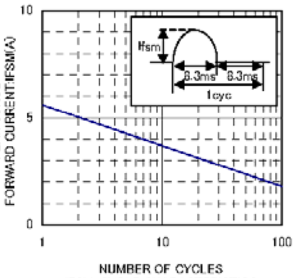
IR DISPERSION MAP



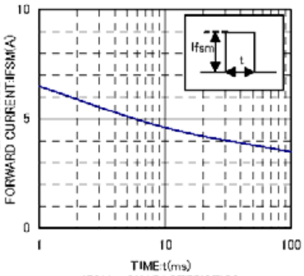
Ct DISPERSION MAP



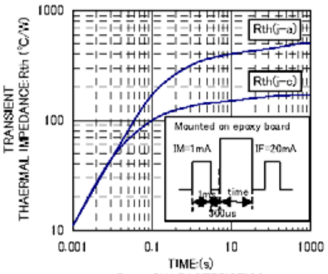
IFSM DISPERSION MAP



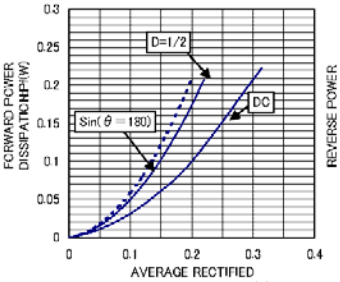
IFSM-CYCLE CHARACTERISTICS



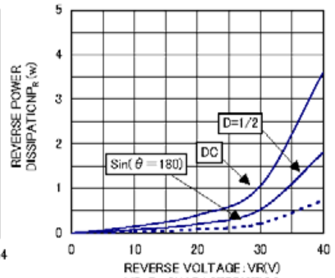
IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS



Io-Pf CHARACTERISTICS



VR-P_R CHARACTERISTICS